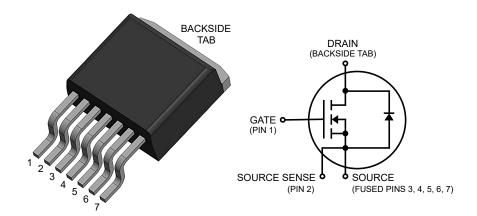
# **700V, 15 mΩ N-Channel mSiC<sup>™</sup> MOSFET**

MSC015SMA070SD



#### **Product Overview**

700V, 15 m $\Omega$  typical at V<sub>GS</sub> = 20V, 17 m $\Omega$  typical at V<sub>GS</sub> = 18V, Silicon Carbide (SiC) N-Channel MOSFET, TO-263 7-lead XL with a source sense.



#### **Features**

- AEC-Q101 qualified option available
- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, T<sub>I(max)</sub> = 175 °C
- · Fast and reliable body diode
- Superior avalanche ruggedness
- · RoHS compliant

#### **Benefits**

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- · Lower system cost of ownership

#### **Applications**

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- · Induction heating and welding
- Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

# 1. Device Specifications

This section shows the specifications of this device.

## 1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V <sub>DSS</sub>	Drain source voltage	700	V
I <sub>D</sub>	Continuous drain current at $T_C = 25$ °C	172	Α
	Continuous drain current at T <sub>C</sub> = 100 °C	121	
I <sub>DM</sub>	Pulsed drain current <sup>1</sup>	450	
$V_{GS}$	Gate-source voltage	23 to -10	V
	Transient gate-source voltage	25 to -12	
P <sub>D</sub>	Total power dissipation at T <sub>C</sub> = 25 °C	692	W
	Linear derating factor	4.5	W/°C

#### Note:

1. Repetitive rating: pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min.	Тур.	Max.	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance	_	0.17	0.22	°C/W
Tj	Operating junction temperature	-55	_	175	°C
T <sub>STG</sub>	Storage temperature	-55	_	175	
_	Reflow temperature	_	_	260	°C
Wt	Package weight	_	1.6	_	g

ESD practices should comply with JESD-625.

#### **1.2** Electrical Performance

The following table shows the static characteristics of this device.  $T_J = 25$  °C unless otherwise specified.

Table 1-3. Static Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$V_{GS} = 0V$ , $I_D = 100 \mu A$	700	_	_	V
R <sub>DS(on)</sub>	Drain-source on resistance <sup>1</sup>	$V_{GS} = 20V, I_D = 40A$	_	15	19	mΩ
		$V_{GS} = 18V, I_D = 40A$	_	17	_	
V <sub>GS(th)</sub>	Gate-source threshold voltage	$V_{GS} = V_{DS}$ , $I_D = 4 \text{ mA}$	1.9	3.0	5.0	V
I <sub>DSS</sub>	Zero gate voltage drain current	$V_{DS} = 700V, V_{GS} = 0V$	_	0.3	35	μΑ
		$V_{DS} = 700V$ , $V_{GS} = 0V$ , $T_{J} = 175$ °C	_	3.5	_	
I <sub>GSS</sub>	Gate-source leakage current	V <sub>GS</sub> = 20V/–10V	_	_	±100	nA

#### Note:

1. Pulse test: pulse width < 380  $\mu$ s, duty cycle < 2%.



The following table shows the dynamic characteristics of this device.  $T_J$  = 25 °C unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating  $V_{GS}$  = 20V/–5V.

Table 1-4. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0V	_	4324	_	pF
C <sub>rss</sub>	Reverse transfer capacitance	V <sub>DD</sub> = 700V	_	44	_	
C <sub>oss</sub>	Output capacitance	$V_{AC} = 25 \text{ mV}$ f = 200 kHz	_	506	_	
$Q_{G}$	Total gate charge	V <sub>GS</sub> = -5V/20V	_	215	_	nC
Q <sub>GS</sub>	Gate-source charge	V <sub>DD</sub> = 470V	_	58	_	
$Q_{GD}$	Gate-drain charge	I <sub>D</sub> = 40A	_	35	_	
t <sub>d(on)</sub>	Turn-on delay time	V <sub>DD</sub> = 470V	<b>—</b>	27	_	ns
t <sub>r</sub>	Voltage rise time	V <sub>GS</sub> = -5V/20V	_	22	_	
t <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 50A	_	40	_	
t <sub>f</sub>	Voltage fall time	$R_{G(ext)} = 4\Omega$	_	12	_	
E <sub>on</sub>	Turn-on switching energy	Freewheeling diode =	_	413	_	μJ
E <sub>off</sub>	Turn-off switching energy	MSC015SMA070SD (V <sub>GS</sub> = -5V); reference Figure 1-18	_	89	_	
ESR	Gate equivalent series resistance	f = 1 MHz, 25 mV, drain short	_	0.69	_	Ω
SCWT	Short circuit withstand time	V <sub>DS</sub> = 560V, V <sub>GS</sub> = 20V	_	3.0	_	μs
E <sub>AS</sub>	Avalanche energy, single pulse	I <sub>D</sub> = 40A	_	6400	_	mJ

The following table shows the body diode characteristics of this device.  $T_J$  = 25 °C unless otherwise specified. The body diode reverse recovery is characterized, not 100% tested.

Table 1-5. Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
$V_{SD}$	Diode forward voltage	$I_{SD} = 40A, V_{GS} = 0V$	_	3.3	_	٧
		I <sub>SD</sub> = 40A, V <sub>GS</sub> = -5V	_	3.6	5.0	
t <sub>rr</sub>	Reverse recovery time	$I_{SD}$ = 50A, $V_{GS}$ = –5V, Drive $R_G$ = $4\Omega$ , $V_{DD}$ =	_	18	_	ns
Q <sub>rr</sub>	Reverse recovery charge	470V, dl/dt = –10900 A/μs	_	1010	_	nC
I <sub>RRM</sub>	Reverse recovery current		_	89	_	Α



# 1.3 Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

Figure 1-1. Drain Current vs.  $V_{DS}$  at  $T_{J}$ 

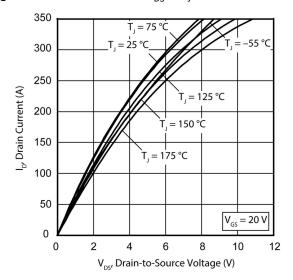


Figure 1-2. Drain Current vs.  $V_{DS}$  at  $V_{GS}$ 

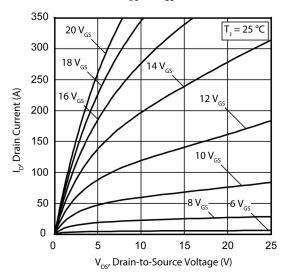


Figure 1-3. Drain Current vs.  $V_{DS}$  at  $V_{GS}$ 

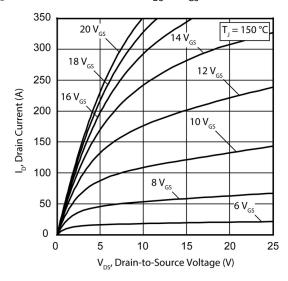


Figure 1-4. Drain Current vs. V<sub>DS</sub> at V<sub>GS</sub>

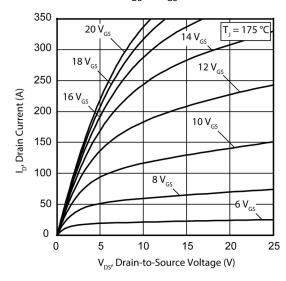


Figure 1-5. R<sub>DS(on)</sub> vs. Junction Temperature

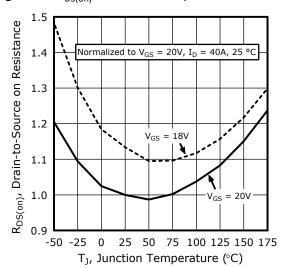


Figure 1-6. Gate Charge Characteristics

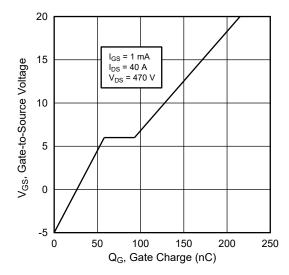


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

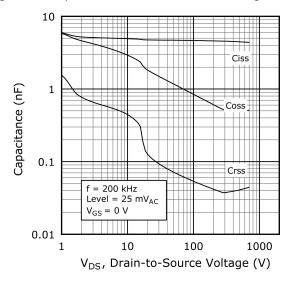


Figure 1-8. Output Charge vs. Drain-to-Source Voltage

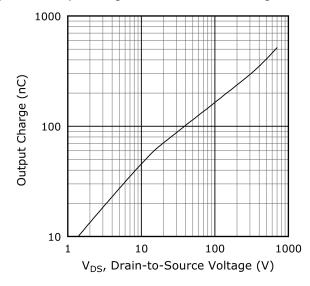




Figure 1-9.  $I_D$  vs.  $V_{DS}$  3<sup>rd</sup> Quadrant Conduction

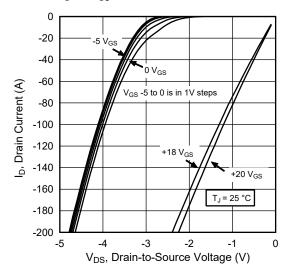
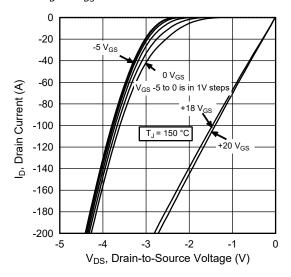
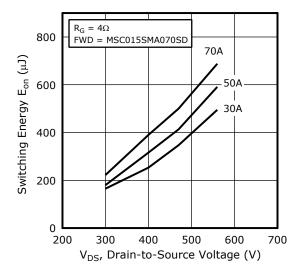


Figure 1-10.  $I_D$  vs.  $V_{DS}$  3<sup>rd</sup> Quadrant Conduction



**Figure 1-11.** Switching Energy  $E_{on}$  vs.  $V_{DS}$  &  $I_{D}$ 



**Figure 1-12.** Switching Energy  $E_{off}$  vs.  $V_{DS} \& I_{D}$ 

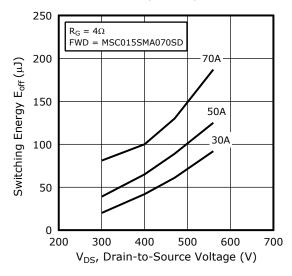




Figure 1-13. Switching Energy vs. R<sub>G</sub>

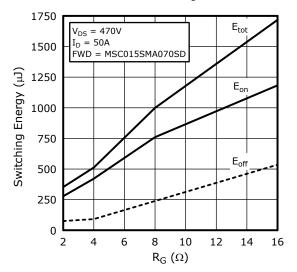


Figure 1-14. Switching Energy vs. Junction Temperature

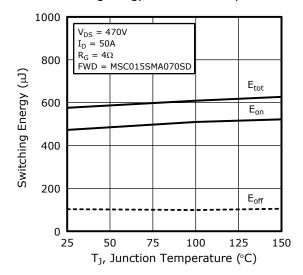
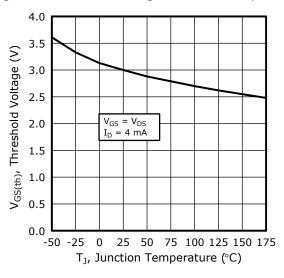


Figure 1-15. Threshold Voltage vs. Junction Temperature Figure 1-16. Forward Safe Operating Area



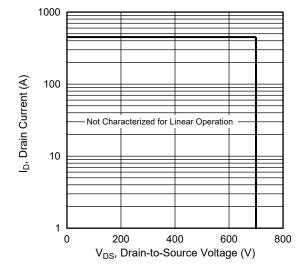
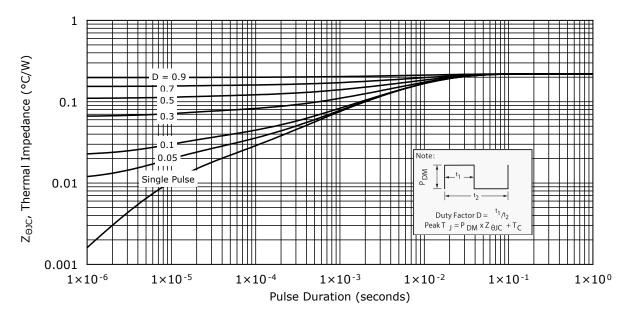


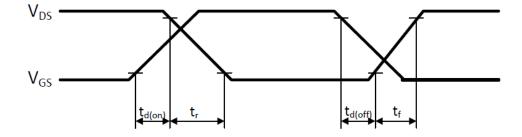


Figure 1-17. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of this device.

Figure 1-18. Switching Waveform





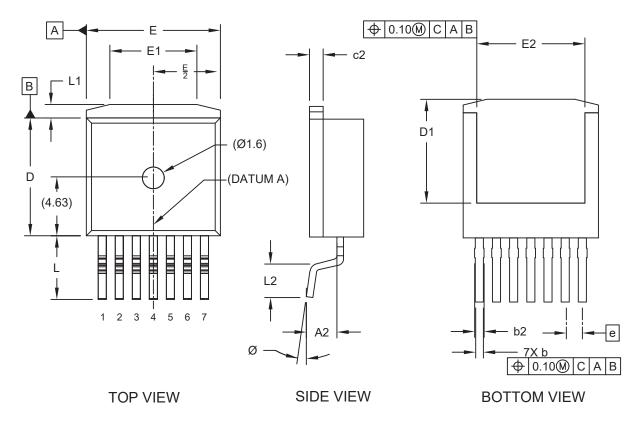
# 2. Package Specification

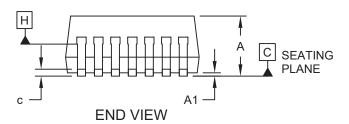
This section shows the package specification of this device.

## 2.1 Package Outline Drawing

The following figure illustrates the TO-263-7L XL package outline of this device.

Figure 2-1. Package Outline Drawing





The following table shows the TO-263-7L XL dimensions and should be used in conjunction with the package outline drawing.

Table 2-1. TO-263-7L XL Dimensions

Symbol	Description	Min. (mm)	Max. (mm)
N	Number of leads	7	
е	Pitch	1.27 BSC	



co	continued					
Symbol	Description	Min. (mm)	Max. (mm)			
Α	Overall height	4.30	4.70			
A1	Seating plane height	_	0.25			
A2	Seating plane to lead	2.20	2.60			
b	Lead width	0.52	0.72			
b1		0.60	0.80			
С	Lead thickness	0.42	0.62			
c2	Thermal pad thickness	1.07	1.47			
L	Lead length	4.55	4.95			
L1	Tab length	0.87	1.27			
L2	Foot length	2.48	2.88			
D	Molded body length	9.05	9.45			
D1	Thermal pad length	7.58	7.98			
Е	Total width	9.80	10.20			
E1	Thermal pad width step back	6.30	6.70			
E2	Thermal pad width	7.80	8.20			
Ø	Lead foot angle	0°	8°			

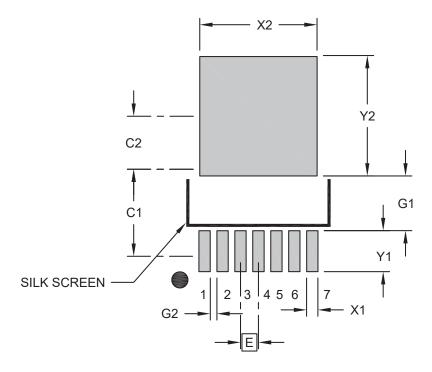
**Note:** Dimensioning and tolerancing per ASME Y14.5M.

• BSC: Basic dimension. Theoretically exact value shown without tolerances.

### 2.2 Recommended Land Pattern

The following figure illustrates the recommended land pattern of this device.

Figure 2-2. Recommended Land Pattern



The following table shows the recommended land pattern dimensions.



Table 2-2. Recommended Land Pattern Dimensions

Symbol	Description	Min. (mm)	Nom. (mm)	Max. (mm)
Е	Contact pitch	1.27 BSC		
X2	Center pad width	_	_	8.30
Y2	Center pad length	_	_	8.45
C1	Contact pad spacing	_	6.45	_
C2	Contact pad spacing	_	4.30	_
X1	Contact pad width (X7)	_	_	0.80
Y1	Contact pad length (X7)	_	_	2.90
G1	Contact pad to center pad (X7)	3.88	_	_
G2	Contact pad to contact pad (X6)	0.47	_	_

#### **Notes:**

- Dimensioning and tolerancing per ASME Y14.5M.
  - BSC: Basic dimension. Theoretically exact value shown without tolerances.
- For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process.



# 3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

Revision	Date	Description
A	09/2024	Initial revision



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